NTTFS4985NF

MOSFET – Power, Single, N-Channel, WDFN8

30 V, 64 A

Features

- Integrated Schottky Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb−Free and are RoHS Compliant

Applications

- CPU Power Delivery
- Synchronous Rectification for DC−DC Converters
- Low Side Switching
- Telecom Secondary Side Rectification

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	T_A = 25°C	I_D	22	A
		T_A = 85°C		15.9	
Power Dissipation $R_{\theta JA}$ (Note 1)		T_A = 25°C	P_D	2.69	W
Continuous Drain Current $R_{\theta JA} \le 10$ s (Note 1)		T_A = 25°C	I_D	32.4	A
		T_A = 85°C		23.4	
Power Dissipation $R_{\theta JA} \le 10$ s (Note 1)		T_A = 25°C	P_D	5.85	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)		T_A = 25°C	I_D	16.3	A
		T_A = 85°C		11.7	
Power Dissipation $R_{\theta JA}$ (Note 2)		T_A = 25°C	P_D	1.47	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)		T_C = 25°C	I_D	64	A
		T_C = 85°C		46	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	22.73	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	192	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to +150	°C
Source Current (Body Diode)			I_S	32	A
Drain to Source dV/dt			dV/dt	6.0	V/ns

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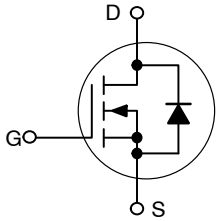
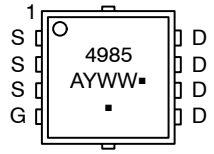
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	3.5 mΩ @ 10 V	64 A
	5.2 mΩ @ 4.5 V	

N−Channel MOSFET



WDFN8
(μ8FL)
CASE 511AB

MARKING DIAGRAM



4985	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTTFS4985NFTAG	WDFN8 (Pb−Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{DD} = 50 V, V_{GS} = 10 V, I_L = 32 A_{pk}, L = 0.1 mH, R_G = 25 Ω)	E_{AS}	52	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface−mounted on FR4 board using 1 sq−in pad, 2 oz Cu.
2. Surface−mounted on FR4 board using the minimum recommended pad size of 90 mm^2.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	5.5	°C/W
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	46.4	
Junction−to−Ambient − Steady State (Note 4)	$R_{\theta JA}$	84.8	
Junction−to−Ambient − (t ≤ 10 s) (Note 3)	$R_{\theta JA}$	21.4	

3. Surface−mounted on FR4 board using 1 sq−in pad, 2 oz Cu.
4. Surface−mounted on FR4 board using the minimum recommended pad size of 90 mm^2.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			500	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.2	1.6	2.3	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.2		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 20 A		2.8	3.5	mΩ
			I_D = 10 A		2.8		
		V_{GS} = 4.5 V	I_D = 20 A		4.16	5.2	
			I_D = 10 A		4.13		
Forward Transconductance	g_{FS}	V_{DS} = 1.5 V, I_D = 10 A			34		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 15 V			2075		pF
Output Capacitance	C_{oss}				876		
Reverse Transfer Capacitance	C_{rss}				46		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 20 A			13.6		nC
Threshold Gate Charge	$Q_{G(TH)}$				2.0		
Gate−to−Source Charge	Q_{GS}				5.8		
Gate−to−Drain Charge	Q_{GD}				4.1		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
CHARGES AND CAPACITANCES							
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 20 A			29.4		nC
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			11		ns
Rise Time	t_r				24		
Turn−Off Delay Time	$t_{d(off)}$				20		
Fall Time	t_f				5.4		
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			8.5		ns
Rise Time	t_r				24		
Turn−Off Delay Time	$t_{d(off)}$				25		
Fall Time	t_f				4.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 2 A	T_J = 25°C		0.4	0.7	V
			T_J = 125°C		0.33		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, d_{IS}/d_t = 100 A/μs, I_S = 2 A			35.7		ns
Charge Time	t_a				18.2		
Discharge Time	t_b				17.5		
Reverse Recovery Charge	Q_{RR}				32		nC
PACKAGE PARASITIC VALUES							
Source Inductance	L_S	T_A = 25°C			0.65		nH
Drain Inductance	L_D				0.20		
Gate Inductance	L_G				1.5		
Gate Resistance	R_G				1.0		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

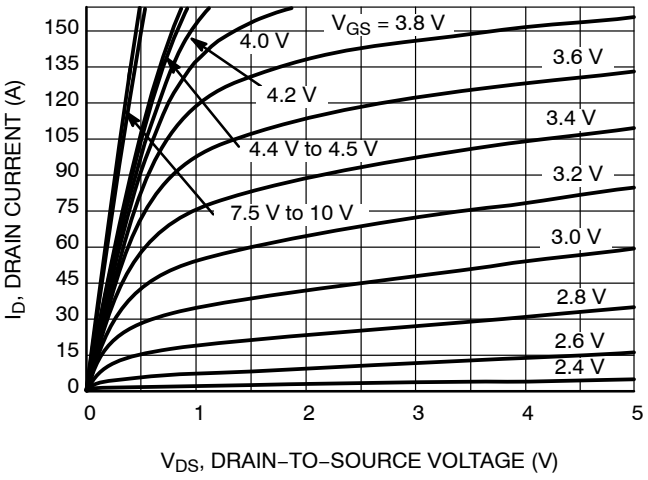


Figure 1. On−Region Characteristics

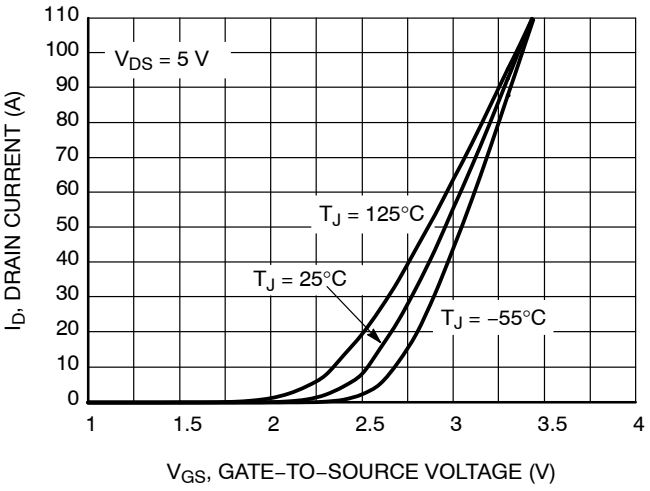


Figure 2. Transfer Characteristics

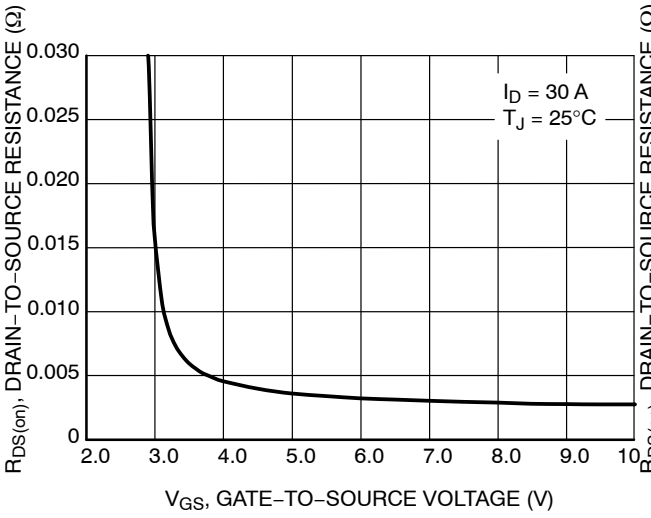


Figure 3. On−Resistance vs. Gate−to−Source Voltage

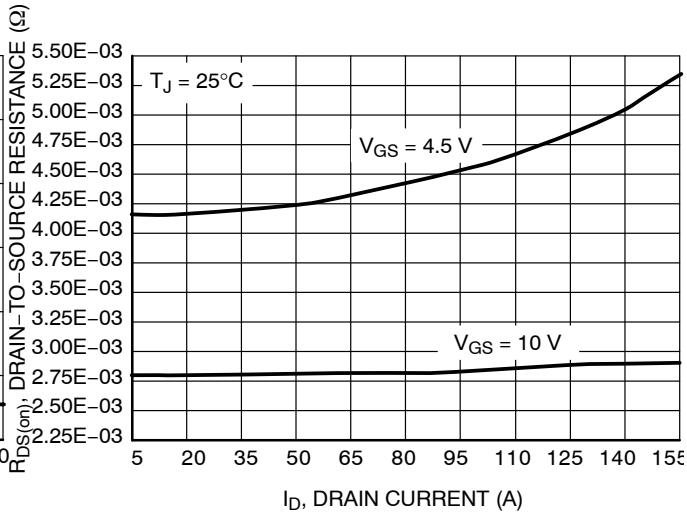


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

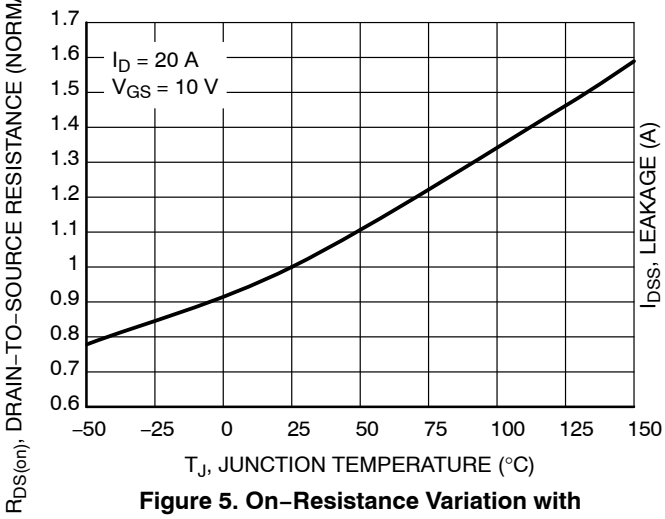


Figure 5. On−Resistance Variation with Temperature

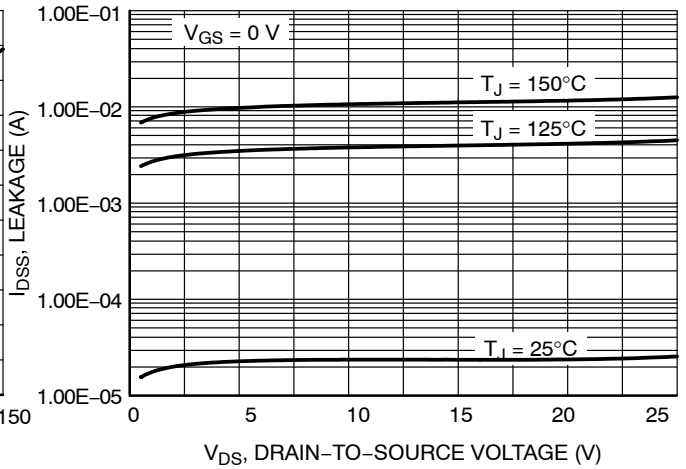


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

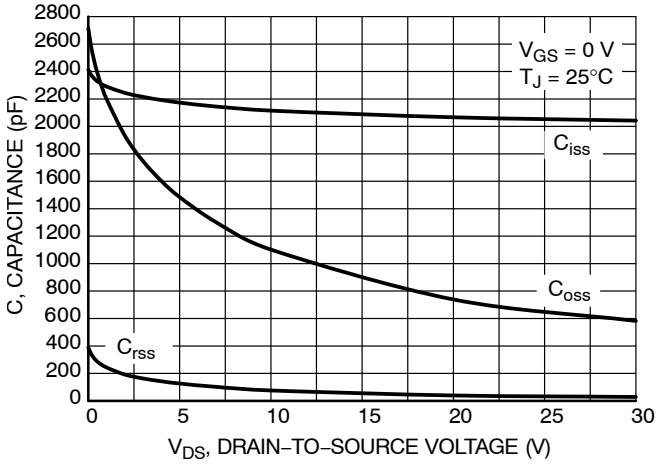


Figure 7. Capacitance Variation

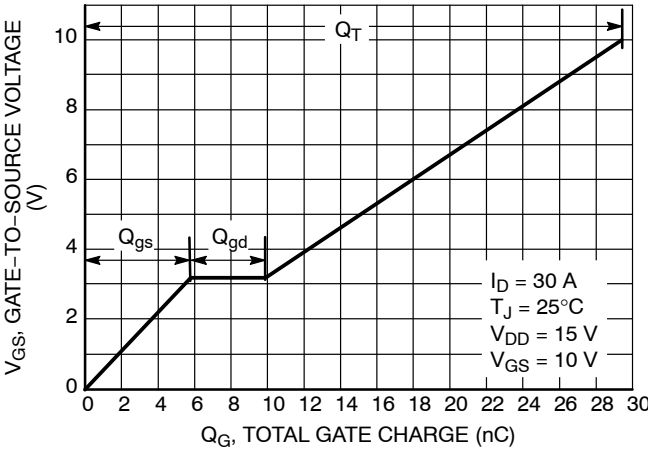


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

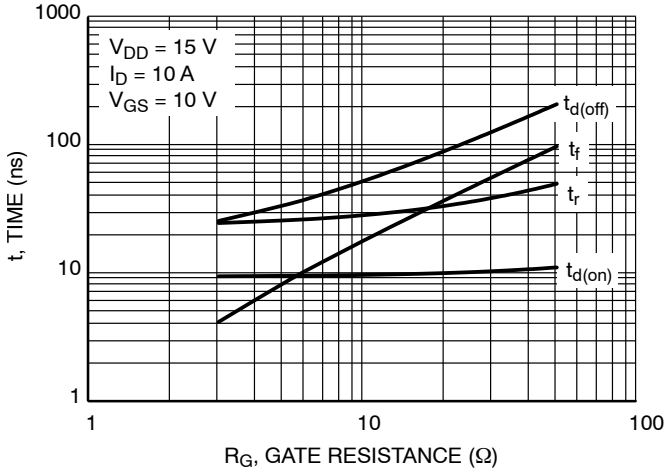


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

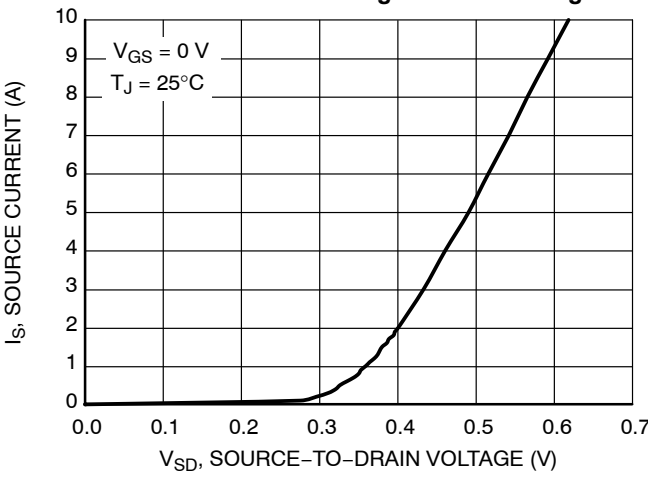


Figure 10. Diode Forward Voltage vs. Current

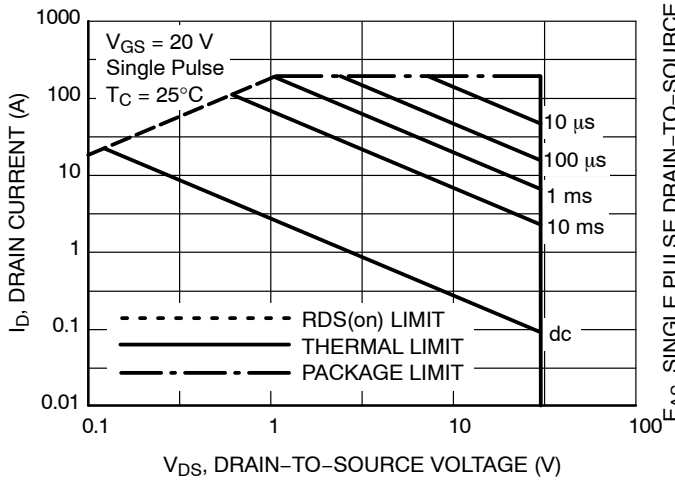


Figure 11. Maximum Rated Forward Biased Safe Operating Area

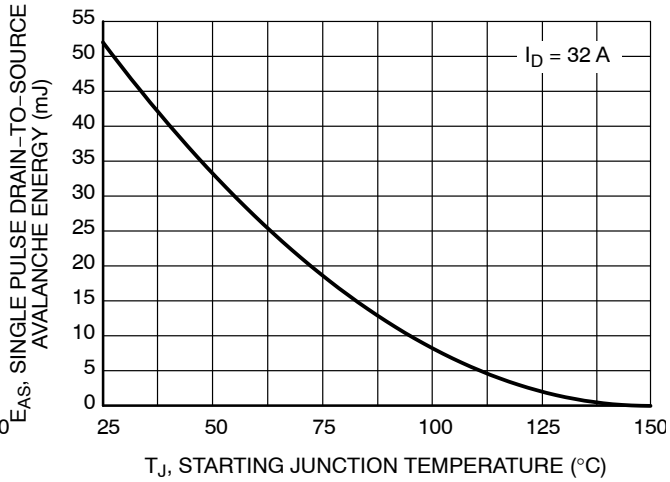


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL PERFORMANCE CURVES

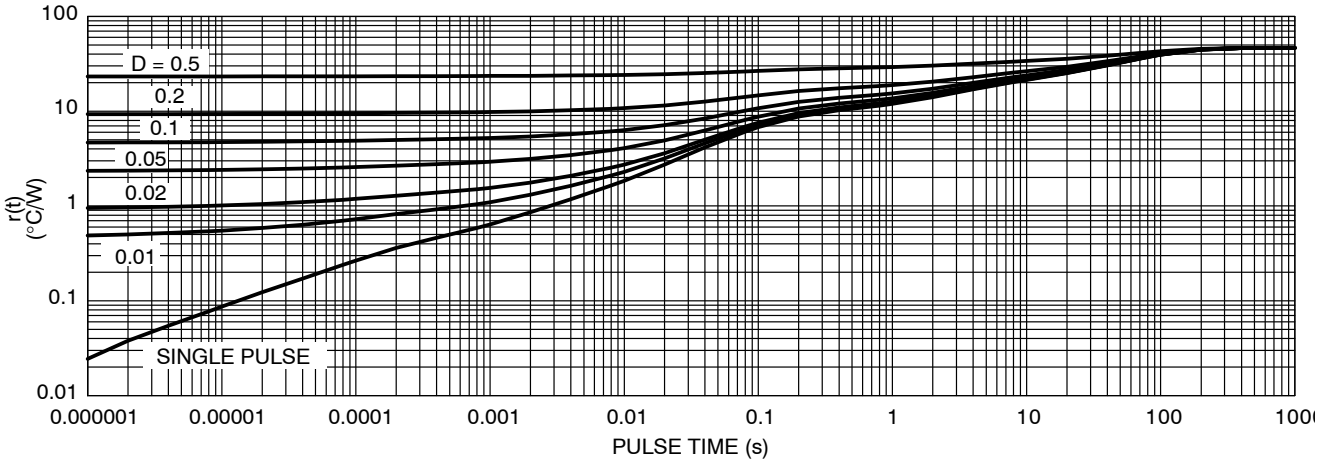


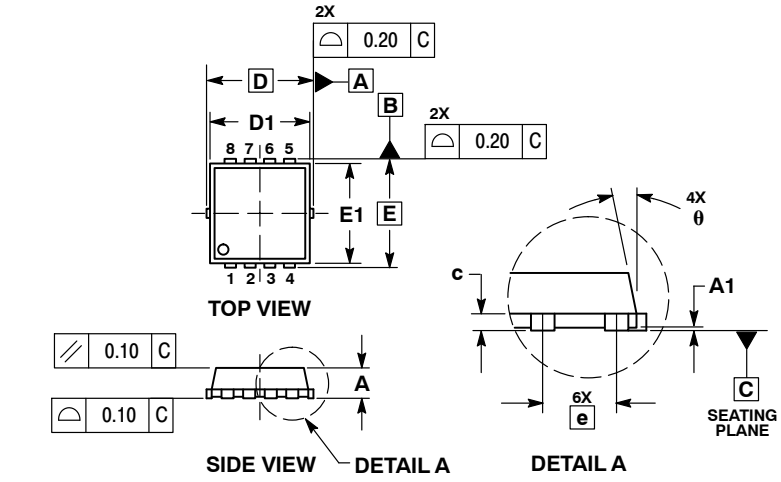
Figure 13. Thermal Response

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SCALE 2:1

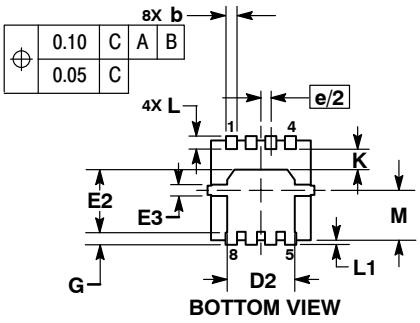
WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

DATE 23 APR 2012

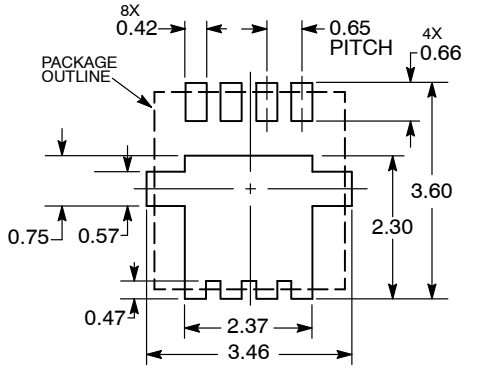


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °



SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**WDFN8 3.3X3.3, 0.65P**	**PAGE 1 OF 1**

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